AMENDMENTS

IN THE ABSTRACT:

CIRCUIT FOR ELECTROSTATIC DISCHARGE PROTECTION

A circuit providing protection against electrostatic discharge (ESD) for internal elements of an Integrated Circuit (IC), is connected to a power rail (VDD) and a ground rail (VSS) and to an inverter (INV) of a clamp preamplifier. The In one example, a protection circuit comprises a PMOSFET resistor (R) with having a gate connected to said a ground rail (VSS), a drain connected to said inverter's (INV) an input node (ESD_RC) of an inverter (INV), a source and a bulk of the PMOSFET resistor (R) being connected to said a power rail (VDD). The circuit also comprises an NMOSFET capacitor (C1) with having a gate connected to said inverter's (INV) the input node (ESD_RC) of the inverter (INV), a drain, a source and a bulk of the NMOSFET capacitor (C1) being connected to said the ground rail (VSS). The circuit also includes and a PMOSFET capacitor (C2) with having a gate connected to said inverter's (INV) the input node (ESD_RC) of the inverter (INV). A drain and a source of the PMOSFET capacitor (C2) being connected to said the ground rail (VSS), and a bulk of the PMOSFET capacitor (C2) is connected to said the power rail (VDD).